

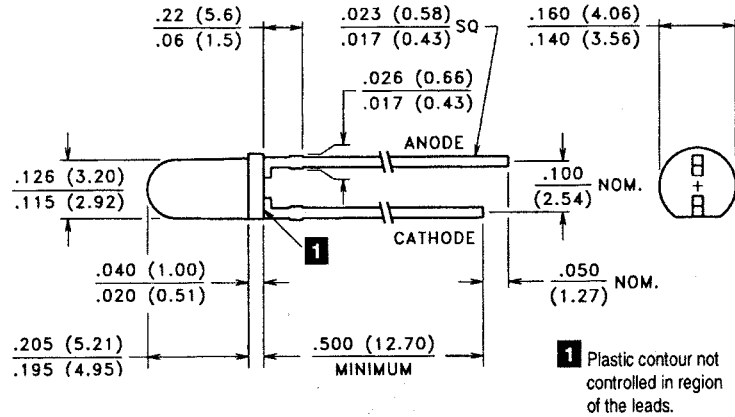
# GaAlAs Infrared Emitting Diodes

Long T-1 (3 mm) Plastic Package — 880 nm

# VTE3372LAH, 74LAH



## PACKAGE DIMENSIONS inch (mm)



CASE 50A Long T-1 (3 mm)  
CHIP SIZE: .011" x .011"

## DESCRIPTION

This narrow beam angle 3 mm diameter plastic packaged emitter is suitable for use in optical switch applications. It contains a small area, GaAlAs, 880 nm, high efficiency IRED die.

## ABSOLUTE MAXIMUM RATINGS @ 25°C (unless otherwise noted) ■

Maximum Temperatures		Maximum Reverse Voltage:	5.0V
Storage and Operating:	-40°C to 100°C	Maximum Reverse Current @ $V_R = 5V$ :	10 $\mu A$
Continuous Power Dissipation:	100 mW	Peak Wavelength (Typical):	880 nm
Derate above 30°C:	1.43 mW/°C	Junction Capacitance @ 0V, 1 MHz (Typ.):	14 pF
Maximum Continuous Current:	50 mA	Response Time @ $I_F = 20$ mA	
Derate above 30°C:	0.71 mA/°C	Rise: 1.0 $\mu s$ Fall: 1.0 $\mu s$	
Peak Forward Current, 10 $\mu s$ , 100 pps:	2.5 A	Lead Soldering Temperature:	260°C
Temp. Coefficient of Power Output (Typ.):	-8%/°C	(1.6 mm from case, 5 seconds max.)	

**RoHS Compliant**



## ELECTRO-OPTICAL CHARACTERISTICS @ 25°C (See also GaAlAs curves, pages 108-110)

Part Number ■	Output						Forward Drop		Half Power Beam Angle	
	Irradiance				Radiant Intensity	Total Power	Test Current	$V_F$		
	$E_e$		Condition		$I_e$	$P_O$	$I_{FT}$	@ $I_{FT}$	$\theta_{1/2}$	
	mW/cm <sup>2</sup>		distance	Diameter	mW/sr	mW	mA (Pulsed)	Volts		Typ.
	Min.	Typ.	mm	mm	Min.	Typ.		Typ.	Max.	
VTE3372LAH	2.0	2.6	10.16	2.1	2.0	3.0	20	1.3	1.8	$\pm 10^\circ$
VTE3374LAH	4.0	5.2	10.16	2.1	4.1	5.0	20	1.3	1.8	$\pm 10^\circ$

■ Refer to General Product Notes, page 2.